

Radar Pulsed Power Transistor 65W, 3.1-3.5 GHz, 100µs Pulse, 10% Duty

M/A-COM Products Released, 10 Aug 07

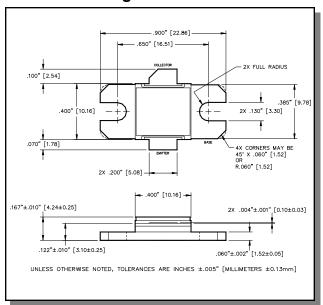
Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ι _C	7.7	Α
Power Dissipation @ +25°C	P _{TOT}	350	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 25mA		BV_CES	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 36V		I _{CES}	-	5.0	mA
Thermal Resistance	Vcc = 36V, Pout = 65W	F = 3.1, 3.3, 3.5 GHz	R _{TH(JC)}	-	0.5	°C/W
Output Power	Vcc = 36V, Pout = 65W	F = 3.1, 3.3, 3.5 GHz	P _{IN}	-	11.6	W
Power Gain	Vcc = 36V, Pout = 65W	F = 3.1, 3.3, 3.5 GHz	G_P	75	-	dB
Collector Efficiency	Vcc = 36V, Pout = 65W	F = 3.1, 3.3, 3.5 GHz	ης	35	-	%
Input Return Loss	Vcc = 36V, Pout = 65W	F = 3.1, 3.3, 3.5 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 65W	F = 3.1, 3.3, 3.5 GHz	VSWR-T	-	2:1	-

Commitment to produce in volume is not guaranteed.

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Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298 Visit www.macomtech.com for additional data sheets and product information.



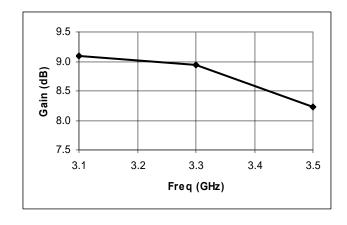
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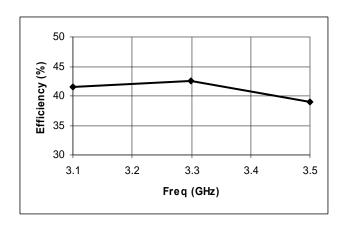
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-T (2:1)
3.1	8.0	65	9.09	4.35	41.5	-10.5	Р
3.3	8.3	65	8.95	4.24	42.6	-9.8	Р
3.5	9.8	65	8.23	4.64	38.9	-17.3	Р

Gain vs. Frequency

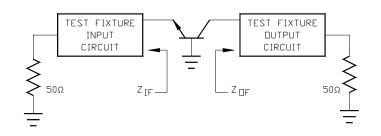


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

F (GHz)	Z _{IF} (Ω)	$Z_{OF}(\Omega)$
3.1	8.9 - j11.2	5.2 - j11.0
3.3	8.7 - j8.6	4.2 - j8.8
3.5	8.6 - j6.0	4.7 - j7.0



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